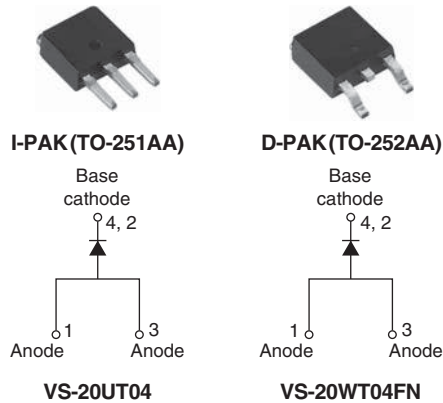


High Performance Schottky Generation 5.0, 20 A



FEATURES

- 175 °C high performance Schottky diode
- Very low forward voltage drop
- Extremely low reverse leakage
- Optimized V_F vs. I_R trade off for high efficiency
- Increased ruggedness for reverse avalanche capability
- RBSOA available
- Negligible switching losses
- Submicron trench technology
- Compliant to RoHS Directive 2002/95/EC


RoHS
COMPLIANT

PRODUCT SUMMARY

Package	D-PAK (TO-252AA), I-PAK (TO-251AA)
$I_{F(AV)}$	20 A
V_R	45 V
V_F at I_F	0.53 V
I_{RM} max.	7 mA at 125 °C
T_J max.	175 °C
Diode variation	Single die
E_{AS}	108 mJ

Note

- V_F measured at 125 °C, connecting 2 anode pins

APPLICATIONS

- Specific for PV cells bypass diode
- High efficiency SMPS
- High frequency switching
- Output rectification
- Reverse battery protection
- Freewheeling
- DC/DC systems
- Increased power density systems

MAJOR RATINGS AND CHARACTERISTICS

SYMBOL	CHARACTERISTICS	VALUES	UNITS
V_{RRM}		45	V
V_F	20 Apk, $T_J = 125$ °C (typical, measured connecting 2 anode pins)	0.480	V
T_J	Range	- 55 to 175	°C

VOLTAGE RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	VS-20UT04 VS-20WT04FN	UNITS
Maximum DC reverse voltage	V_R	$T_J = 25$ °C	45	V

VS-20UT04, VS-20WT04FN



Vishay Semiconductors

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ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum average forward current	$I_{F(AV)}$	50 % duty cycle at $T_C = 153\text{ }^\circ\text{C}$, rectangular waveform		20	A
Maximum peak one cycle non-repetitive surge current	I_{FSM}	5 μs sine or 3 μs rect. pulse	Following any rated load condition and with rated V_{RRM} applied ⁽¹⁾	900	A
		10 ms sine or 6 ms rect. pulse		220	
Non-repetitive avalanche energy	E_{AS}	$T_J = 25\text{ }^\circ\text{C}$, $I_{AS} = 7\text{ A}$, $L = 4.4\text{ mH}$		108	mJ
Repetitive avalanche current	I_{AR}	Limited by frequency of operation and time pulse duration so that $T_J < T_{J\text{max}}$. I_{AS} at $T_{J\text{max}}$ as a function of time pulse		I_{AS} at $T_{J\text{max}}$.	A

Note

⁽¹⁾ Measured connecting 2 anode pins

ELECTRICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS		TYP.	MAX.	UNITS
Forward voltage drop	V_{FM} ⁽¹⁾⁽²⁾	10 A	$T_J = 25\text{ }^\circ\text{C}$	0.505	0.540	V
		20 A		0.570	0.610	
		10 A	$T_J = 125\text{ }^\circ\text{C}$	0.415	0.450	
		20 A		0.520	0.580	
Reverse leakage current	I_{RM} ⁽¹⁾	$T_J = 25\text{ }^\circ\text{C}$	$V_R = \text{Rated } V_R$	-	100	μA
		$T_J = 125\text{ }^\circ\text{C}$		-	7	mA
Junction capacitance	C_T	$V_R = 5\text{ }V_{DC}$ (test signal range 100 kHz to 1 MHz), $25\text{ }^\circ\text{C}$		1900	-	pF
Series inductance	L_S	Measured lead to lead 5 mm from package body		-	-	nH
Maximum voltage rate of change	dV/dt	Rated V_R		-	10 000	V/ μs

Notes

- ⁽¹⁾ Pulse width < 300 μs , duty cycle < 2 %
- ⁽²⁾ Only 1 anode pin connected

THERMAL - MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum junction and storage temperature range	T_J, T_{Stg}			- 55 to 175	$^\circ\text{C}$
Maximum thermal resistance, junction to case	R_{thJC}	DC operation		1.2	$^\circ\text{C/W}$
Typical thermal resistance, case to heatsink	R_{thCS}			0.3	
Approximate weight				2	g
				0.07	oz.
Marking device		Case style I-PAK		20UT04	
		Case style D-PAK		20WT04FN	

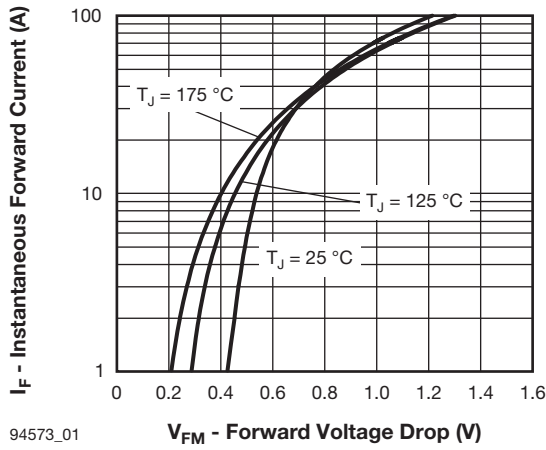


Fig. 1 - Maximum Forward Voltage Drop Characteristics

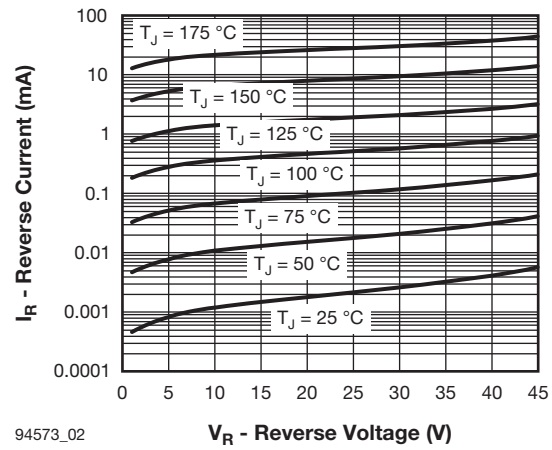


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

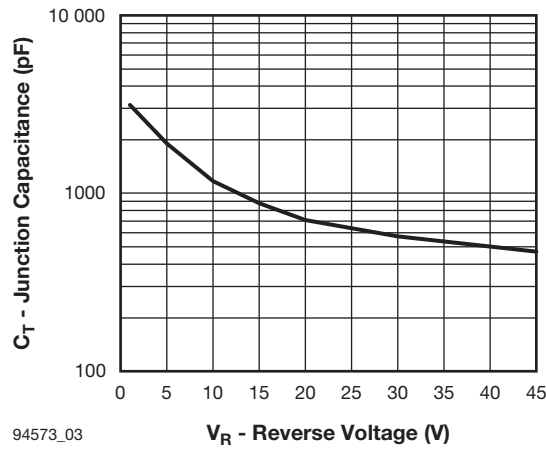


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

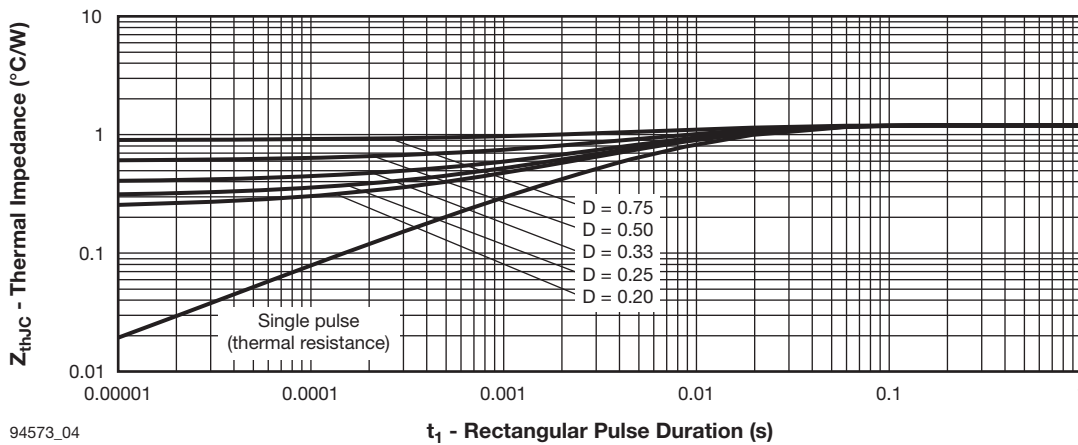


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

VS-20UT04, VS-20WT04FN



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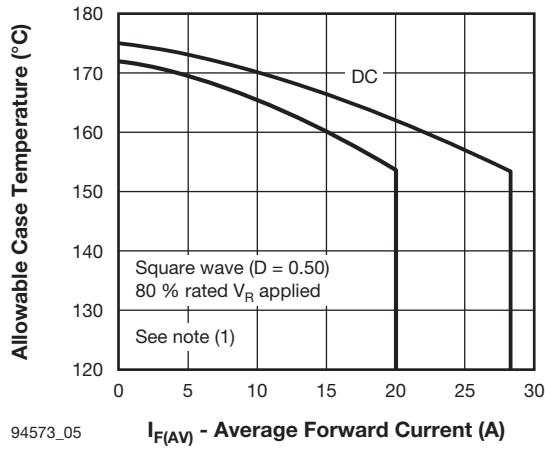


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

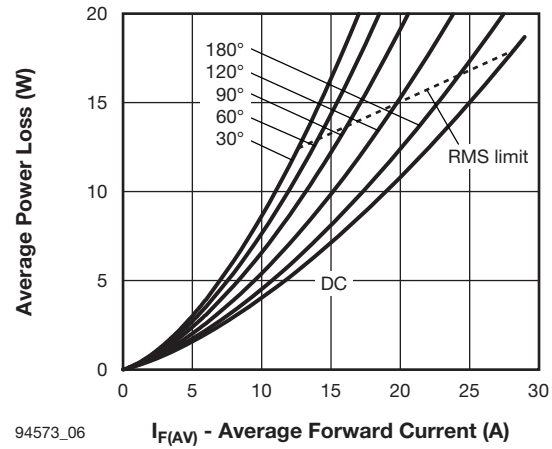


Fig. 6 - Forward Power Loss Characteristics

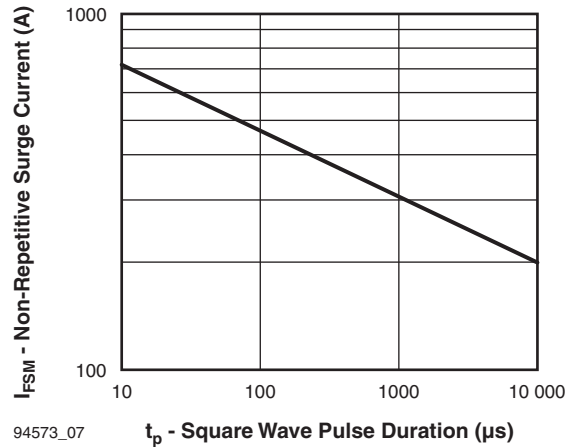
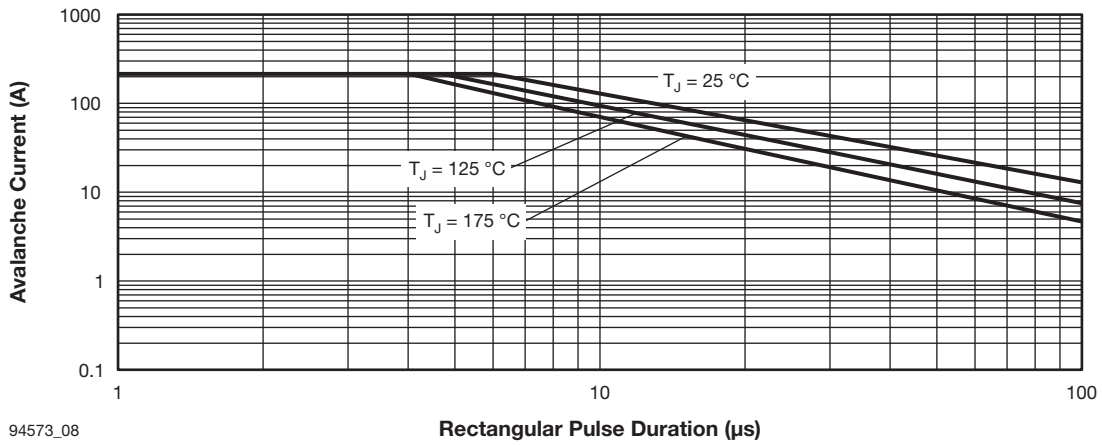


Fig. 7 - Maximum Non-Repetitive Surge Current

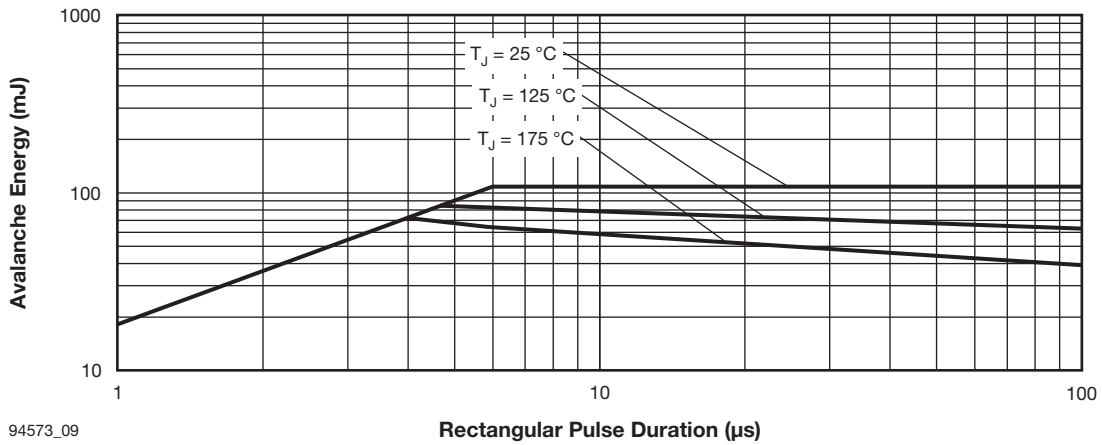
Note

- (1) Formula used: $T_C = T_J - (P_d + P_{d_{REV}}) \times R_{thJC}$;
 P_d = Forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 6);
 $P_{d_{REV}}$ = Inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at $V_{R1} = 80\%$ rated V_R



94573_08

Fig. 8 - Reverse Bias Safe Operating Area (Avalanche Current vs. Rectangular Pulse Duration)



94573_09

Fig. 9 - Reverse Bias Safe Operating Area (Avalanche Energy vs. Rectangular Pulse Duration)

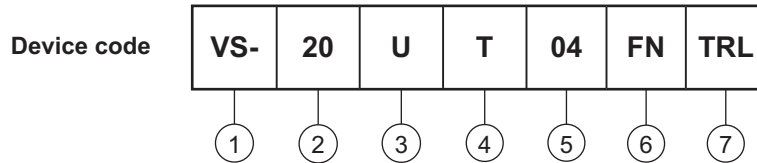
VS-20UT04, VS-20WT04FN

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High Performance Schottky
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ORDERING INFORMATION TABLE

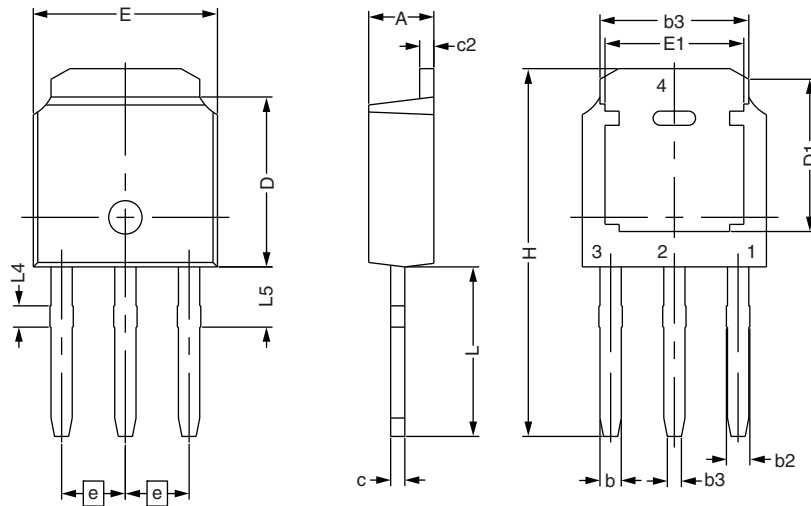


- 1** - Vishay Semiconductors product
- 2** - Current rating (20 A)
- 3** - Package:
 - U = I-PAK
 - W = D-PAK
- 4** - T = Trench
- 5** - Voltage code (45 V)
- 6** - TO-252AA (D-PAK)
- 7** - D-PAK, I-PAK:
 - None = Tube (75 pieces)
 - D-PAK only:
 - TR = Tape and reel
 - TRL = Tape and reel (left oriented)
 - TRR = Tape and reel (right oriented)

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95024
Part marking information	www.vishay.com/doc?95025
Packaging information	www.vishay.com/doc?95033
SPIICE model	www.vishay.com/doc?95027

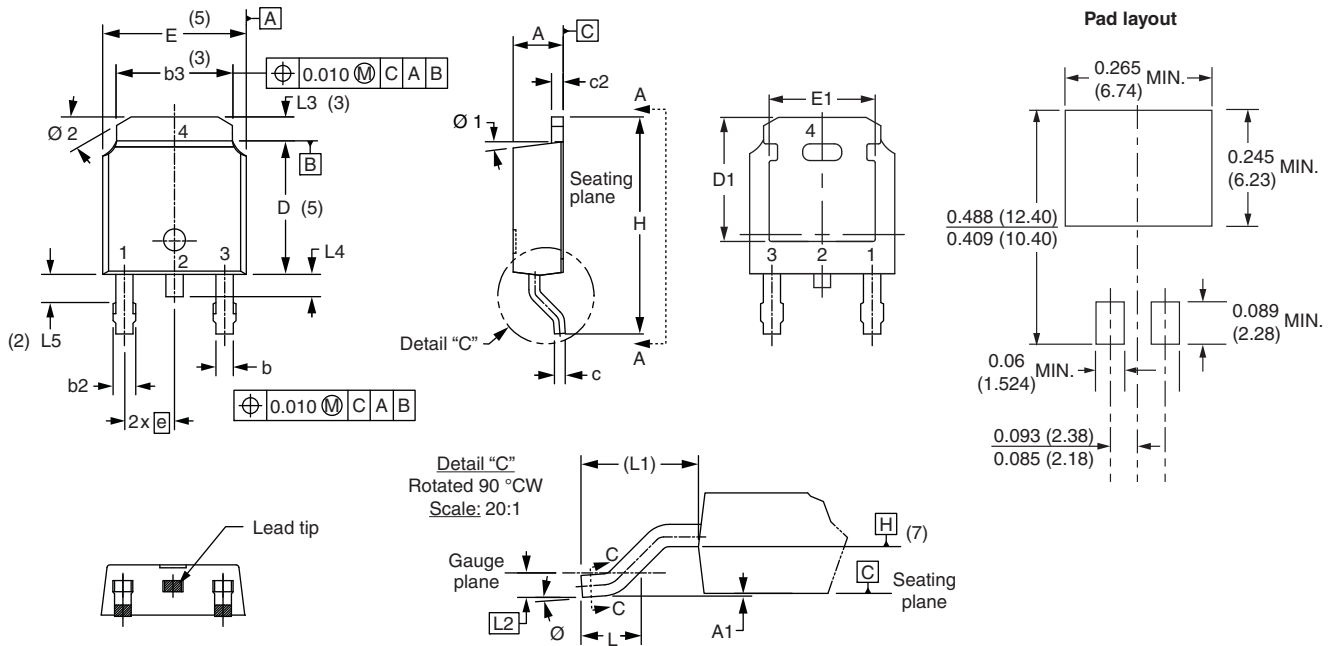
I-PAK - S, D-PAK

DIMENSIONS FOR I-PAK - S in millimeters



SYMBOL	DIMENSIONAL REQUIREMENTS		
	MIN.	NOM.	MAX.
E	6.40	6.60	6.70
L	3.98	4.13	4.28
L4	0.66	0.76	0.86
L5	1.96	2.16	2.36
D	6.00	6.10	6.20
H	11.05	11.25	11.45
b	0.64	0.76	0.88
b2	0.77	0.84	1.14
b3	5.21	5.34	5.46
b4	0.41	0.51	0.61
e	2.286 BSC		
A	2.20	2.30	2.38
c	0.40	0.50	0.60
c2	0.40	0.50	0.60
D1	5.30	-	-
E1	4.40	-	-

DIMENSIONS FOR D-PAK in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.			MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	0.086	0.094		e	2.29 BSC		0.090 BSC		
A1	-	0.13	-	0.005		H	9.40	10.41	0.370	0.410	
b	0.64	0.89	0.025	0.035		L	1.40	1.78	0.055	0.070	
b2	0.76	1.14	0.030	0.045		L1	2.74 BSC		0.108 REF.		
b3	4.95	5.46	0.195	0.215	3	L2	0.51 BSC		0.020 BSC		
c	0.46	0.61	0.018	0.024		L3	0.89	1.27	0.035	0.050	3
c2	0.46	0.89	0.018	0.035		L4	-	1.02	-	0.040	
D	5.97	6.22	0.235	0.245	5	L5	1.14	1.52	0.045	0.060	2
D1	5.21	-	0.205	-	3	Ø	0°	10°	0°	10°	
E	6.35	6.73	0.250	0.265	5	Ø1	0°	15°	0°	15°	
E1	4.32	-	0.170	-	3	Ø2	25°	35°	25°	35°	

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension uncontrolled in L5
- (3) Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad
- (4) Section C - C dimension apply to the flat section of the lead between 0.13 and 0.25 mm (0.005 and 0.10") from the lead tip
- (5) Dimension D, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (6) Dimension b1 and c1 applied to base metal only
- (7) Datum A and B to be determined at datum plane H
- (8) Outline conforms to JEDEC outline TO-252AA



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